

## WHAT IS CLAIMED IS:

1. A substrate processing apparatus spraying gas to a substrate completely cleaned with deionized water for drying said substrate, comprising:

5           a first gas discharge element spraying said gas to the surface of said substrate wet with said deionized water; and

              a second gas discharge element further spraying said gas to the same region as the region already sprayed with said gas by said first gas discharge element.

10           2. The substrate processing apparatus according to claim 1, wherein the flow rate of said gas sprayed from said second gas discharge element to said substrate is larger than the flow rate of said gas sprayed from said first gas discharge element to said substrate.

15           3. The substrate processing apparatus according to claim 2, further comprising a rotation element rotating said substrate substantially in a horizontal plane, wherein

              said first gas discharge element comprises:

              a first nozzle discharging said gas, and

20           a first nozzle moving element moving said first nozzle substantially in a horizontal plane,

              said second gas discharge element comprises:

              a second nozzle discharging said gas, and

25           a second nozzle moving element moving said second nozzle substantially in a horizontal plane, and

said first nozzle moving element and said second nozzle moving element move the respective ones of said first nozzle and said second nozzle so that arrival points of said gas discharged from the respective ones of said first nozzle and said second nozzle draw loci directed from the rotation center of rotated said substrate toward the edge.

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4. The substrate processing apparatus according to claim 3, wherein said gas is inert gas.

5. A substrate processing apparatus spraying gas to a substrate completely 10 cleaned with deionized water for drying said substrate, comprising:

a first nozzle spraying said gas to the surface of said substrate wet with said deionized water;

a second nozzle spraying said gas to the surface of said substrate;

a nozzle arm fixedly provided with said first nozzle and said second nozzle;

15 and

a moving element moving said nozzle arm in a plane substantially parallel to said substrate, wherein

said moving element moves said nozzle arm to spray said gas from said second nozzle to the same region as the region on said substrate sprayed with said gas by said 20 first nozzle.

6. The substrate processing apparatus according to claim 5, wherein the flow rate of said gas sprayed from said second nozzle to said substrate is larger than the flow rate of said gas sprayed from said first nozzle to said substrate.

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7. The substrate processing apparatus according to claim 6, further comprising a rotation element rotating said substrate substantially in a horizontal plane, wherein

5        said moving element moves said nozzle arm substantially in a horizontal plane so that arrival points of said gas discharged from the respective ones of said first nozzle and said second nozzle draw loci directed from the rotation center of rotated said substrate toward the edge.

10      8. The substrate processing apparatus according to claim 7, wherein said gas is inert gas.

9. A substrate processing apparatus spraying gas to a substrate completely cleaned with deionized water for drying said substrate, comprising:

15      a nozzle spraying said gas to the surface of said substrate wet with said deionized water;

      a nozzle arm fixedly provided with said nozzle; and

      a moving element moving said nozzle arm in a plane substantially parallel to said substrate, wherein

20      said moving element moves said nozzle arm to re-spray said gas from said nozzle to the same region as the region on said substrate sprayed with said gas by said nozzle.

10. The substrate processing apparatus according to claim 9, wherein the flow rate of said gas re-sprayed from said nozzle to said substrate is larger 25     than the flow rate of said gas precedently sprayed from said nozzle to said substrate.

11. The substrate processing apparatus according to claim 10, further comprising a rotation element rotating said substrate substantially in a horizontal plane, wherein

5           said moving element moves said nozzle arm substantially in a horizontal plane so that arrival points of said gas precedently and subsequently discharged from said nozzle draw loci directed from the rotation center of rotated said substrate toward the edge.

10           12. The substrate processing apparatus according to claim 11, wherein said gas is inert gas.

13. A substrate processing method spraying gas to a substrate completely cleaned with deionized water for drying said substrate, comprising steps of:

15           a) spraying said gas to the surface of said substrate wet with said deionized water; and  
                 b) further spraying said gas to the same region as the region on said substrate already sprayed with said gas in said step a).

20           14. The substrate processing method according to claim 13, wherein the flow rate of said gas sprayed to said substrate in said step b) is larger than the flow rate of said gas sprayed to said substrate in said step a).

25           15. The substrate processing method according to claim 14, wherein said gas is inert gas.